

# Product data sheet

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Compiance

SOT-23

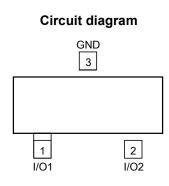
#### Features

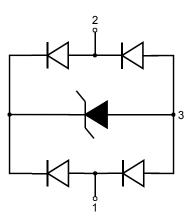
- Stand-off voltage: 5V Max
- Transient protection for each line according to IEC61000-4-2 (ESD): ±20kV (contact and air discharge) IEC61000-4-4 (EFT): 40A (5/50ns) IEC61000-4-5 (surge): 4A (8/20µs)
- Ultra-low capacitance: C<sub>J</sub> = 0.4pF typ.
- Ultra-low leakage current: I<sub>R</sub> <1nA typ.
- Low clamping voltage: V<sub>CL</sub> = 20V @ I<sub>PP</sub> = 16A(TLP)
- Solid-state silicon technology

#### **Applications**

- USB 2.0 and USB 3.0
- HDMI 1.3 and HDMI 1.4
- SATA and eSATA
- DVI
- IEEE 1394
- PCI Express
- Portable Electronics
- Notebooks









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Parameter	Symbol	Rating	Unit	
Peak pulse power ( $t_p = 8/20\mu s$ )	P <sub>pk</sub>	60	W	
Peak pulse current (t <sub>p</sub> = 8/20µs)	I <sub>PP</sub>	4	A	
ESD according to IEC61000-4-2 air discharge	N/	±20	kV	
ESD according to IEC61000-4-2 contact discharge	– V <sub>ESD</sub>	±20		
Junction temperature	TJ	125	°C	
Operating temperature	T <sub>OP</sub>	-40~85	°C	
Lead temperature	TL	260	°C	
Storage temperature	T <sub>STG</sub>	-55~150	°C	

## Electrical characteristics (T<sub>A</sub>=25 °C, unless otherwise noted)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Reverse maximum working voltage	V <sub>RWM</sub>				5.0	V
Reverse leakage current	I <sub>R</sub>	V <sub>RWM</sub> = 5V		<1	100	nA
Reverse breakdown voltage	V <sub>BR</sub>	I⊤ = 1mA	7.0	8.0	9.0	V
Forward voltage	VF	I <sub>T</sub> = 10mA	0.6	0.9	1.2	V
Clamping voltage <sup>1)</sup>	V <sub>CL</sub>	I <sub>PP</sub> = 16A, t <sub>p</sub> = 100ns		20		V
Dynamic resistance 1)	R <sub>DYN</sub>			0.65		Ω
Clemping voltage 2	V <sub>CL</sub>	I <sub>PP</sub> = 1A, t <sub>p</sub> = 8/20μs			11	V
Clamping voltage <sup>2)</sup>		$I_{PP} = 4A, t_p = 8/20 \mu s$			15	V
	on capacitance CJ	V <sub>R</sub> = 0V, f = 1MHz		0.40	0.65	pF
lunction capacitance		Any I/O pin to GND		0.40		
		V <sub>R</sub> = 0V, f = 1MHz		0.25	0.40	pF
		Between any I/O pin		0.25		

Notes:

1) TLP parameter:  $Z_0 = 50 \Omega$ ,  $t_p = 100$ ns,  $t_r = 2$ ns, averaging window from 60 ns to 80 ns.  $R_{DYN}$  is calculated from 4A to 16A.

2) According to IEC61000-4-5.

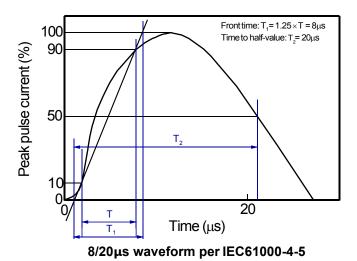


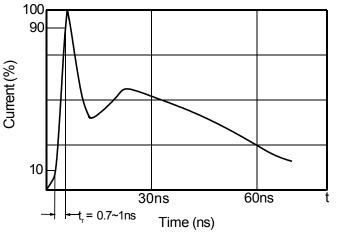
Vc - Clamping voltage (V)

AZC199-02S-MS HF (

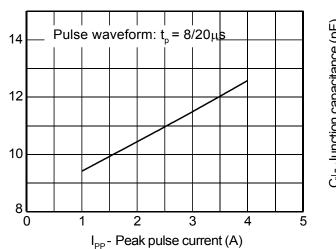
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#### Typical characteristics (T<sub>A</sub>=25°C, unless otherwise noted)

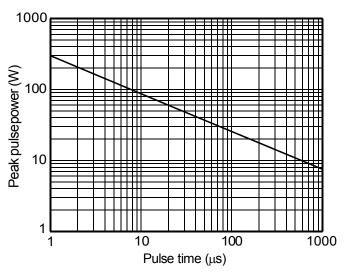




Contact discharge current waveform per IEC61000-4-2



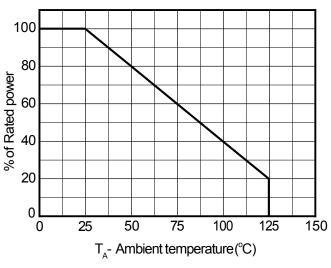
Clamping voltage vs. Peak pulse current



Non-repetitive peak pulse power vs. Pulse time

0.50 C<sup>J</sup> - Junction capacitance (pF) f = 1MHz 0.45 Pin1 or 2 to Pin3 0.40 0.35 0.30 Between Pin1 and Pin2 0.25 0.20 2 3 0 1 4 5  $V_{R}$ - Reverse voltage (V)

Capacitance vs. Reverse voltage



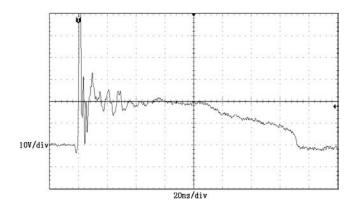
Power derating vs. Ambient temperature



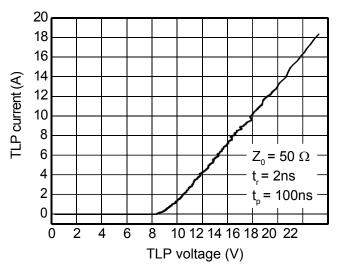


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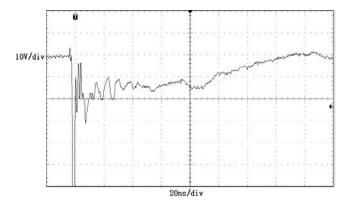
## Typical characteristics (T<sub>A</sub>=25°C, unless otherwise noted)



ESD clamping (+8kV contact discharge per IEC61000-4-2)



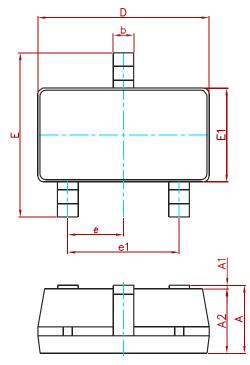
**TLP Measurement** 

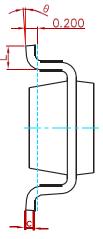


ESD clamping (-8kV contact discharge per IEC61000-4-2)



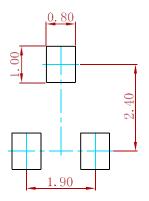
#### PACKAGE MECHANICAL DATA





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E1	1.500	1.700	0.059	0.067	
E	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(1	(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
0	0°	8°	0°	8°	

# Suggested Pad Layout



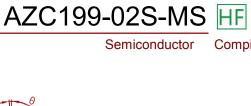
Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.

3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
AZC199-02S-MS	SOT-23	3000



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